

BYV10MED-650P

Ultrafast power diode Rev.01 - 14 December 2023

**Product data sheet** 

### **1. General description**

Ultrafast power diode in a TO252 (DPAK) plastic package



### 2. Features and benefits

- Fast switching
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT
- Package meets UL94 V0 which guaranteed by Epoxy Mold Compound

### 3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Power Factor Correction (PFC)

### 4. Quick reference data

Symbol	Parameter	Conditions	Notes	s Values			Unit
Absolute	maximum rating						
V <sub>RRM</sub>	repetitive peak reverse voltage			650			V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 114 °C; Fig. 1; Fig. 2; Fig. 3		10		A	
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 114 °C; square-wave pulse		20			A
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse; <u>Fig. 4</u>		95			A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		104.5			А
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	1.43	2.00	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.20	1.60	V
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>i</sub> = 25 °C; <u>Fig. 7</u>		-	27	-	ns

## 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected		к_И_А
2	К	cathode [1]		K — — — A 001aaa020
3	А	anode		
mb	К	mounting base; connected to cathode		

[1] It is not possible to connect to pin 2 of the TO252 package.

## 6. Ordering information

### Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYV10MED-650P	TO252	BYV10MED-650PJ	Reel	2500	TO252d	07-Sep-2022

### 7. Marking

### Table 4. Marking codes

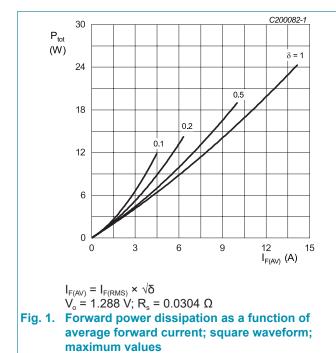
Type number	Marking codes
BYV10MED-650P	BYV10MED
	650P

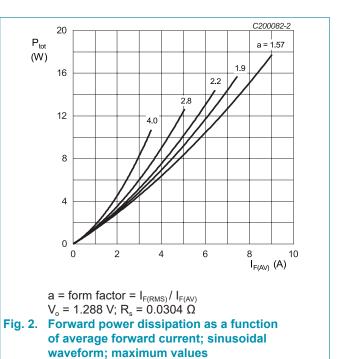
## 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

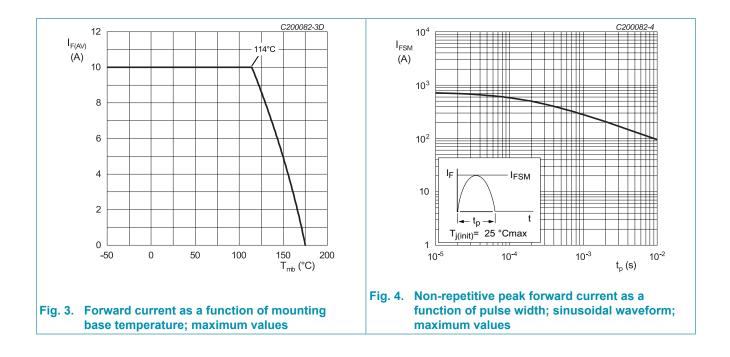
Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{\text{RRM}}$	repetitive peak reverse voltage			650	V
$V_{\text{RWM}}$	crest working reverse voltage			650	V
V <sub>R</sub>	reverse voltage	DC		650	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 114 °C; Fig. 1; Fig. 2; Fig. 3		10	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 114 °C; square-wave pulse		20	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		95	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		104.5	А
$T_{stg}$	storage temperature			-65 to 175	°C
Tj	junction temperature			-65 to 175	°C





Ultrafast power diode

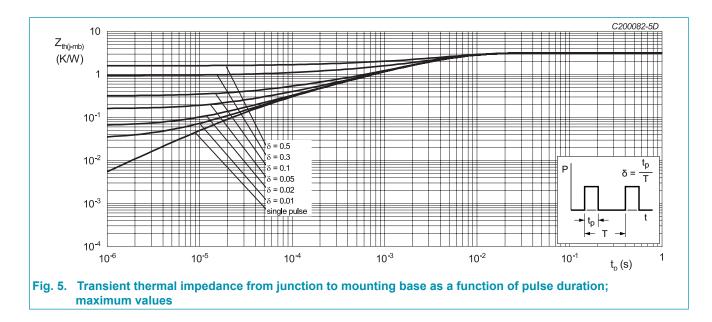
BYV10MED-650P



## 9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	3.2	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	[2]	-	50	-	K/W

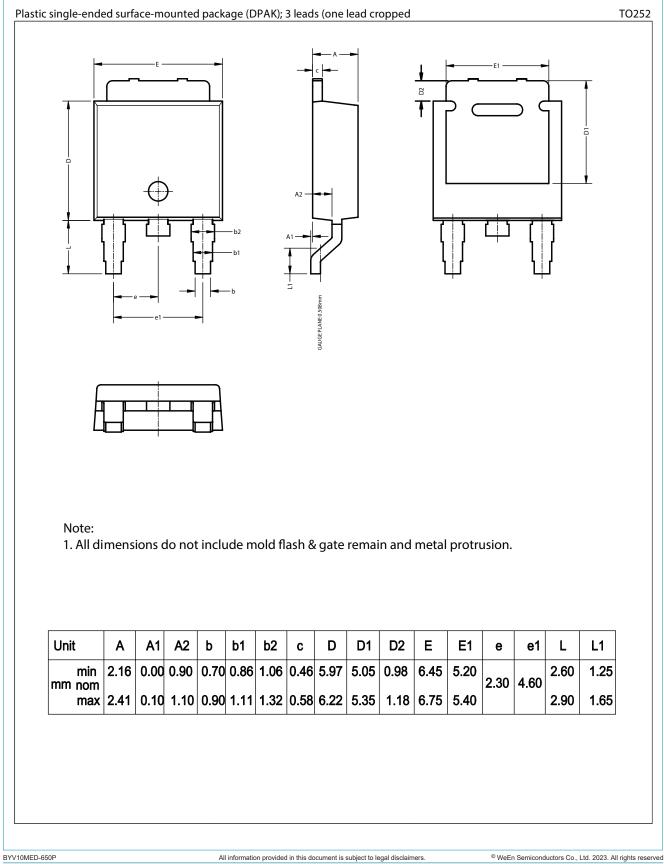
[2] Device mounted on an FR4 PCB, single-sided copper, tin plated and standard footprint.



### **10. Characteristics** Table 7 Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	1.43	2.00	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.20	1.60	V
R	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C		-	0.13	8	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C		-	-	0.4	mA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C		-	0.27	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C		-	-	0.5	mA
Dynamic	characteristics		I				
Q <sub>r</sub>	reverse charge	$I_{F} = 10 \text{ A};  V_{R} = 200 \text{ V};  dI_{F}/dt = 200 \text{ A}/\mu\text{s}; \\ T_{j} = 25 ^{\circ}\text{C};  \underline{\text{Fig. } 7}$		-	141	-	nC
		$I_{F} = 10 \text{ A};  V_{R} = 200 \text{ V};  dI_{F}/dt = 200 \text{ A}/\mu\text{s}; \\ T_{j} = 125 ^{\circ}\text{C};  \underline{\text{Fig. } 7}$		-	357	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{rr} = 0.25 \text{ A}; T_j = 25 \text{ °C}$	;	-	30	-	ns
		$I_{F} = 1 \text{ A};  V_{R} = 30 \text{ V};  dI_{F}/dt = 100 \text{ A}/\mu\text{s}; \\ T_{j} = 25 \text{ °C}; \text{ Fig. 7}$		-	27	-	ns
		$I_{F} = 10 \text{ A};  V_{R} = 200 \text{ V};  dI_{F}/dt = 200 \text{ A}/\mu\text{s}; \\ T_{j} = 25 \text{ °C};  \underline{Fig. 7}$		-	53	-	ns
		$I_{F} = 10 \text{ A}; V_{R} = 200 \text{ V}; \text{ d}I_{F}/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_{j} = 125 ^{\circ}\text{C}; \text{ Fig. 7}$		-	84	-	ns
I <sub>RM</sub> peak reverse recovery current		$I_{F} = 10 \text{ A}; \text{ V}_{R} = 200 \text{ V}; \text{ d}I_{F}/\text{d}t = 200 \text{ A}/\mu\text{s}; \\ T_{j} = 25 \text{ °C}; \text{ Fig. 7}$		-	5.3	-	A
		$I_{F} = 10 \text{ A}; \text{ V}_{R} = 200 \text{ V}; \text{ d}I_{F}/\text{d}t = 200 \text{ A}/\mu\text{s}; \\ T_{j} = 125 ^{\circ}\text{C}; \text{ Fig. 7}$		-	8.5	-	A
E <sub>as</sub>	non-repetitive analanche energy	T <sub>j(init)</sub> = 25 °C		20	-	-	mJ
I <sub>F</sub> (A)	20 15 10 10 10 10 10 10 10 10 10 10	$I_F$ $I_R$	_	- t <sub>rr</sub>	•	25	time % 100 9 Jaac562
(1 (2 (3	) = 1.288 V; R <sub>s</sub> = 0.0304 Ω ) T <sub>j</sub> = 150 °C; typical valu 2) T <sub>j</sub> = 150 °C; maximum va 3) T <sub>j</sub> = 25 °C; maximum va orward current as a func-	2 es ralues lues Fig. 7. Revers	se recovery	y defini	tions; rai	mp reco	very

### 11. Package outline



# BYV10MED-650P

### Ultrafast power diode

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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# BYV10MED-650P

### **13. Contents**

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	5
10. Characteristics	6
11. Package outline	7
12. Legal information	8
13. Contents	10

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